Tunneling Conductance and Coulom b B lockade Peak Splitting of Two Quantum Dots Connected by a Quantum Point Contact

Yu-Liang Liu

M ax-P lanck-Institut für Physik K om plexer System e, Bayreuther Str. 40, D-01187 D resden,
G erm any

A bstract

By using bosonization method and unitary transformation, we give a general relation between the dimensionless tunneling conductance and the fractional Coulomb blockade conductance peak splitting which is valid both for weak and strong transmission between two quantum dots, and show that the tunneling conductance has a linear temperature dependence in the low energy and low temperature limit.

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E lectron tunneling in a mesoscopic structure may be drastically in uenced by the charging e ects. If the charge spreading is impeded by weak links, or by a special geometry of the structure, the charging suppresses the electron tunneling. Such a suppression of the electron tunneling is commonly called as the Coulomb blockade [1,2,3]. It has become possible to observe the Coulomb blockade e ect in sem iconductor heterostructures where the geometry of the system can be easily modied by adjusting the voltages on special gate electrodes. Recently, the electron tunneling through two quantum dots connected by single quantum point contact which is controlled by adjusting voltage on additional gate electrode has been extensively studied, both experimental [4,5,6,7,8] and theoretical [9,10,11,12,13]. The electron tunneling between two quantum dots leads to a decay of the Coulomb blockade of the individual dot. For a pair of electrostatically identical quantum dots, the progress of this decay can be described by tracking the splitting of the Coulomb blockade conductance peaks as they evolve from doubly degenerate single-dot conductance resonances to that of nondegenerate double-dot peaks with twice the original periodicity. The Coulomb blockade peak splitting signi cantly depends upon the transmission coe cient T of the quantum point contact, i.e., the tunneling conductance. For the case of T = 1, the Coulom b blockade between two quantum dots disappears, they become a double-quantum dot. For the case of T = 0, the Coulomb blockade is maximum which completely suppresses the electron tunneling between two quantum dots, therefore, they are separated from each other.

In this paper, by using bosonization method and unitary transform ation developed in Ref. [14], we can electively treat the system of two electrostatically identical quantum dots connected by one quantum point contact which is controlled by adjusting voltage on additional gate electrode, and give a general relation between the dimensionless tunneling conductance g and the fractional Coulomb blockade peak splitting f, which is valid both for weak (T 0) and strong (T 1) transmission coefficients. We also study the temperature dependence of the tunneling conductance in the low energy and low temperature limit.

In generally, each individual quantum dot can be described by two-dimensional electron gas, and the Coulomb charging energy $E_c = e^2 = (2C)$, where C is the capacitance of the

individual quantum dot, is very large compared to the single-particle level spacing but small compared to the tunneling channel band-widths. For the case of only a few modes can tunnel from one quantum dot to another one, the quantum point contact can be described by a quantum wire [15,16]. We can also use a potential barrier to adjust the transmission coe cient. Based upon above considerations, we consider the following Hamiltonians [15,16,17]

$$H_{0} = ihv_{F}^{X} dx [_{R}^{+} (x) \theta_{x R} (x) _{L}^{+} (x) \theta_{x L} (x)]$$
 (1)

$$H_{c} = E_{c} \left(\hat{n} - \frac{N}{2} \right)^{2} \tag{2}$$

$$H_{I} = V_{2k_{f}}$$
 [$_{R}^{+}$ (0) $_{L}$ (0) + $_{L}^{+}$ (0) $_{R}$ (0)] (3)

where $_R$ (x) are right-moving electron operators, $_L$ (x) are left-moving electron operators; $E_c=e^2=(2C)$, $eN=C_g(V_{gR}-V_{gL})$ is the gate voltage parameter of two quantum dots, and C_g is a gate-to-dot capacitance. $ef=(e=2)^{P} {R_1 \atop 0} dx [{1 \atop R} (x) {R_1} (x) {1 \atop L} (x) {1 \atop L} (x)]$ is the charge difference between two quantum dots; V_{2k_F} is a backward scattering potential which controls the transmission coefcient T. The system described by these Hamiltonians (1), (2) and (3) has been extensively studied by directly using the bosonization representation of the electron elds $_{R(L)}$ (x) in the strategy of perturbation methods. However, the backward scattering term is relevant in the term inology of the renormalization group, the perturbation method may fail. To more electronly study this problem, we adopt another way developed in Ref. [14] where the backward scattering term can be exactly cancelled by an unitary transformation, and its electronly enterpression of the charge operator eff. We define the following new ferm ion elds

$$_{1} (x) = \frac{1}{2} [_{R} (x) + _{L} (x)]; \quad _{2} (x) = \frac{1}{2} [_{R} (x) _{L} (x)]$$
 (4)

while the bosonic representation of these ferm ion elds can be written in the usual way [18,19,20] as

$$_{1(2)}$$
 $(x) = (\frac{D}{2 \text{ hy}_{r}})^{1=2} e^{\frac{1}{1(2)}(x)}$ (5)

where D is the band width of the conduction electrons. The boson elds $_{1(2)}$ (x) have the relation with the density operators $@_{x=1(2)}$ (x) = $_{1(2)}$ (x), and satisfy the commutation relations $@_{x=1}$ (x); $_{1} \circ (y)$] = $_{1} \circ (x - y)$, $@_{x=2}$ (x); $_{2} \circ (y)$] = $_{1} \circ (x - y)$, where the density operators are defined as $_{1(2)}$ (x) = $_{1(2)}^{+}$ (x) $_{1(2)}$ (x). The Ham iltonians (1) and (3) can be written in the bosonic representation of the ferm ion elds $_{1(2)}$ (x) as

$$H_0 = \frac{hv_F}{4} X^{X}^{Z} dx [(\theta_{x-1})^2 + (\theta_{x-2})^2]$$
 (6)

$$H_{I} = \frac{hv_{F}}{2} X [\theta_{x-1} (x) \theta_{x-2} (x)]_{\dot{x}=0}$$
 (7)

where = $\arctan(V_{2k_F} = (hv_F))$ is phase shift induced by the backward scattering potential. A coording to Eq.(4), the charge operator en can be written as

which only includes the cross term softhe ferm ion elds $_1$ (x) and $_2$ (x).

In order to cancel the term in (7), we do not be following unitary transform ation

$$U = \exp f_{\frac{1}{2}}^{X} [_{1} (0) _{2} (0)]g$$
 (9)

Under this unitary transform ation, we can obtain the following relations

$$U^{+} (H_{0} + H_{I})U = H_{0}$$

 $H_{c} = U^{+} H_{c}U = E_{c} [U^{+} \hat{n} U \frac{N}{2}]^{2}$ (10)

It is worth notice that the backward scattering term completely disappears, its e ect is only rejected on the charge operator en for this problem. It has not any in uence on the correlation functions of the ferm ion elds $_{1(2)}$ (x) because we do not consider the electron-electron interactions in the quantum wire. The calculation of U^+ $\hat{n}U$ is very simple. By using the following formulae

$$[\ _{1} \ (x); \ _{1} \circ (y)] = i \quad \circ sgn (x \quad y); \quad [\ _{2} \ (x); \ _{2} \circ (y)] = i \quad \circ sgn (x \quad y)$$

$$U^{+} _{1} \ (x)U = _{1} \ (x) + \frac{1}{2} sgn (x); \quad U^{+} _{2} \ (x)U = _{2} \ (x) \quad \frac{1}{2} sgn (x)$$

$$(11)$$

and taking the following gauge transform ations

$$_{1}(x) = _{1}(x)e^{i_{1}}; \quad _{2}(x) = _{2}(x)e^{i_{2}}; \quad _{1} \quad _{2} =$$
 (12)

we can easily obtain the following expression of the charge operator eU^+ $\mathrm{fl}\mathrm{U}$

$$U^{+} \hat{\Pi} U = \hat{\Pi} + \frac{\cos(2)}{2} \quad dx \begin{bmatrix} 1 \\ 1 \end{bmatrix} (x) \quad 2 \quad (x) + \quad \frac{1}{2} \quad (x) \quad 1 \quad (x) \end{bmatrix}$$

$$i \frac{\sin(2)}{2} \quad dx \begin{bmatrix} 1 \\ 1 \end{bmatrix} (x) \quad 2 \quad (x) \quad \frac{1}{2} \quad (x) \quad 1 \quad (x) \end{bmatrix}$$
(13)

It is noted that although the backward scattering term is elim inated by the unitary transform ation U (9), the charge operator eU⁺ fiU becomes complex. To simplify it, we re-de no the right-and left-moving electronic elds

$$_{R} (x) = \frac{1}{2} [_{1} (x) + _{2} (x)]; \quad _{L} (x) = \frac{1}{2} [_{1} (x) _{2} (x)]$$
 (14)

while their bosonic representations reads $_{R(L)}$ (x) = $(\frac{D}{2 \text{ hv}_F})^{1=2} \exp f$ i $_{R(L)}$ (x)g. These new right- and left-moving electronic elds are dierent from original ones due to we have taken the unitary and gauge transformations of the fermion elds $_{1(2)}$ (x). In terms of these new electronic elds, the charge operator $eU^+ \hat{n}U$ can be rewritten as

where n = $(1=(4))^P$ [$\cos(2)_R$ (1) + $_R$ (1) $_L$ (1) $\cos(2)_L$ (1)]. If we take the value of the phase shift as c = =2, we can obtain the following relation

$$U^{+} \hat{n} U j_{c} = n_{c} = \frac{1}{2}^{X} (N_{L} N_{R})$$
 (16)

where $N_{R(L)} = {R_1 \atop 1} dx {+ \atop R(L)} (x) {R(L)} (x)$ are the right- and left-moving electron numbers, respectively. Therefore, the value of the phase shift ${}^c = {}^c =$

coupling critical point of the system induced by the backward scattering potential. At this strong coupling critical point, the transm ission coe cient T of the electrons from the left quantum dot to the right one (or vice versa) is zero, i.e., the electrons are completely rejected on the impurity site x=0. These two quantum dots are completely separated, therefore, we can observe a series of the double degenerate C oulomb blockade conductance peaks at this strong coupling critical point.

We now study the low temperature behavior of the tunneling conductance and the fractional Coulomb blockade conductance peak splitting away from this strong coupling critical point ($^{c} = = 2$). Because the directly hopping of the electrons from the right of the impurity to its left or vice versa is very weak, we can approximately replace the quantity

$$\stackrel{Z}{\underset{0}{\longrightarrow}} dx \left[\stackrel{+}{\underset{L}{\longrightarrow}} (x) _{R} (x) \stackrel{+}{\underset{R}{\longrightarrow}} (x) _{L} (x) \right]$$

by

$$a[_{T}^{+}(0)_{R}(0)_{R}(0)]$$

where a is a small constant. For simplicity, we de ne the following new boson elds

$$_{c}(x) = \frac{1}{2}[_{L"}(x) + _{L\#}(x) (_{R"}(x) + _{R\#}(x))]$$

$$_{s}(x) = \frac{1}{2}[_{L"}(x) \quad _{L\#}(x) \quad (_{R"}(x) \quad _{R\#}(x))]$$

In terms of these new boson elds, the charge operator eU + fiU is

$$U^{+} \hat{n} U = n + \frac{\cos(2) + 1}{2} c(0) + \frac{aD \sin(2)}{hv_{r}} \sin(c_{c}(0)) \cos(c_{s}(0))$$
(17)

and the Hamiltonian (6) reads

$$H_{0} = \frac{hv_{F}}{4}^{Z} dx [(\theta_{x} + c(x))^{2} + (\theta_{x} + c(x))^{2} + (\theta_{x} - c(x))^{2} + (\theta_{x} - c(x))^{2} + (\theta_{x} - c(x))^{2}]$$
(18)

However, due to the quantity a sin (2) is very small, the last term in (17) can be perturbatively treated, the electrostatic Hamiltonian (10) can be written as by using Eq.(17)

$$H_{c} = E_{c} \left[\frac{\cos(2) + 1}{2} \right]_{c} (0) \qquad N_{c}^{2} + E_{c} \left(\frac{aD \sin(2)}{hv_{c}} \right)^{2} \sin^{2}(c_{c}(0)) \cos^{2}(c_{s}(0))$$
 (19)

where N = n + N = 2. It is worth noting that for the case of weak backward scattering 0, i.e., the transmission coe cient T = 1, the low temperature behavior of the system is dierent from that for the strong backward scattering. We retronsider the case of the weak backward scattering 0. Because the factor $(\cos(2) + 1) = (2)$ is nite, the boson eld $_{c}(0)$ has a non-zero expectation value

$$\frac{\cos(2) + 1}{2} < c(0) > = N$$
 (20)

which suppresses its low energy excitations. Therefore, we can safely integrate out the boson eld $_{\rm c}$ (0) and obtain the following elective H am iltonian

$$H_{c}^{0} = E_{c} \left(\frac{aD \sin(2)}{2 \text{ hy}_{c}}\right)^{2} \left[1 - \left(\frac{4 \text{ e } E_{c}}{D}\right)^{2} \cos(2 < c(0) >)\right] \left[1 + \cos(2 c(0))\right]$$
(21)

where $E_c = E_c (1 + \cos(2))^2 = (2)^2$, and '0:577 is Euler constant. However, in the ferm ionization representation, $\cos(2_s(0))$ can be written as: $\cos(2_s(0))$ + (0^+) + (

For the case of the strong backward scattering =2, the electrostatic energy significantly depends upon the quantity N. If N is zero, N=0, after integrating out the boson eld $_{c}(0)$, we can obtain the following electrostatic H am iltonian

$$H_{c}^{0} = E_{c} \left(\frac{\text{aD sin (2)}}{2 \text{ hv}_{F}}\right)^{2} \left[1 - \left(\frac{4 \text{ e } E_{c}}{D}\right)^{2}\right] \left[1 + \cos(2 - \sin(0))\right]$$
 (22)

For the case of N \in 0, because of M ax ($_{c}$ (0))j= , if the phase shift satis es the relation: j j $_{0}$, where $_{0}$ is de ned as: $1 + \cos(2_{0}) = 2$ N, after integrating out the boson eld $_{c}$ (0), we can obtain the same H am iltonian as that in (21). If the phase shift satis es the relation: $_{0}$ < j j =2, we can obtain the following e ective H am iltonian

$$H_{c}^{0} = E_{c} \left[\frac{\cos(2) + 1}{2} < c(0) > N \right]^{2} + E_{c} \left(\frac{aD \sin(2)}{2 \text{ hv}_{E}} \right)^{2} \left[1 + \left(\frac{4 \text{ e } E_{c}}{D} \right)^{2} \right] \left[1 + \cos(2 \text{ s}(0)) \right]$$
(23)

where < $_{c}(0) >=$ for N > 0, and < $_{c}(0) >=$ for N < 0. It is worth notice that the present method used to get the nale ective H am iltonians in (21), (22) and (23) is completely different from that in Refs. [15] and [21]. After performing the unitary transformation (9), all information of the conduction electron scattering on the impurity is incorporated into the electrostatic H am iltonian (19) which only contains higher order terms of the boson elds $_{c(s)}(0)$. However, in Refs. [15] and [21], the authors directly take the approximation on the backward scattering potential which leads to a lower order terms of the boson elds $_{c(s)}(0)$. This difference may make us obtain a different transport behavior from that in Ref. [21] in the low temperature limit. On the other hands, in terms of the term inology of the renormalization group, the former only gives some irrelevant terms, but the latter gives some relevant terms. Based upon above discussions, for the case of 0 j j 0, we can obtain the following ground state energy of the system

$$E = E_0 E_c (\frac{2ae E_c \sin (2)}{hv_F})^2 \cos (2 < c(0) >)$$
 (24)

For the case of $_0 < j j = 2$, the ground state energy of the system reads

$$E = E_0 + E_c[j N j \frac{1}{2}(\cos(2) + 1)]^{\frac{2}{3}}$$

$$E_c(\frac{2ae E_c \sin(2)}{hv_c})^{\frac{2}{3}}$$
(25)

Now we can obtain the fractional Coulomb blockade conductance peak splitting [13]. For the case of 0 $\,$ j j $\,$ 0, it can be written as

$$f = \mathbb{E} (N = \frac{1}{2}) \quad \mathbb{E} (N = 0) = \mathbb{E} (N = \frac{1}{2}; c = \frac{1}{2})$$

$$= 4 \left(\frac{2ae \, \mathbb{E}_c \sin(2)}{hv_F}\right)^2 \left(\frac{1 + \cos(2)}{2}\right)^4 \left(1 - \cos(\frac{1 + \cos(2)}{1 + \cos(2)}\right)$$
(26)

In the case of $_0 < j j = 2$, it can be written as

$$f = 4\left[\frac{1}{2} \quad \frac{1}{2} (1 + \cos(2))\right]^{2} \tag{27}$$

It is noted that the fractional Coulomb blockade conductance peak splitting signi cantly depends upon the phase shift , i.e., the transmission coe cient T. However, in the case of

the weak backward scattering 0 $\,$ j j $\,$ 0, it also denpends upon the parameter a, the Ferm i velocity v_F and the electrostatic C oulomb energy $E_c=e^2=(2C)$. In the case of the strong backward scattering $_0<$ j j =2, the fractional C oulomb blockade conductance peak splitting f only depends upon the phase shift , therefore, it is universal.

We now study the low temperature behavior of the tunneling conductance. To this end, we de ne the following current operator

$$I = e\theta_{t} (U^{+} \hat{n} U) = e^{\frac{1 + \cos(2)}{2}} \theta_{t c} (0)$$

$$\frac{\text{aeD } \sin(2)}{\text{hv}_{t}} [\theta_{t c} (0) \cos(c_{c} (0)) \cos(c_{s} (0)) - \theta_{t s} (0) \sin(c_{c} (0)) \sin(c_{s} (0))]$$
(28)

U sing the K ubo form ula of the conductance, we can easily obtain the following tunneling conductance in the low energy and low temperature limit

$$G(T) = G_0()[1 + AT(\frac{\sin(2)}{\cos(2)})^2 \cos(2) < c(0) > 0]$$
 (29)

where $G_0() = e^2(1+\cos(2))^2 = (4 \text{ h})$, T is the tem perature, and A is a constant. It is noted that the tunneling conductance has a linear tem perature dependence, and at the strong coupling critical point $^c = = 2$, it is equal to zero. It is necessary to mention that as the frequency! and the tem perature T tend to zero, the system approaches to the strong coupling critical point delta^c = = 2 because the backward scattering term is relevant, the renormalized backward scattering potential V_{2k_F} tends to in nity in the low energy limit [22].

W e de ne the following dimensionless tunneling conductance

$$g = \frac{G(0)}{G_0} = \frac{1}{2} (1 + \cos(2))^2$$
 (30)

where $G_0 = e^2 = (2 \text{ h})$ is a unit quantum conductance of each tunneling channel. From Equs. (26) and (27), we can obtain the following relation between the dimensionless tunneling conductance q and the fractional Coulomb blockade peak splitting f

$$f = \begin{cases} 8 & p - \frac{1}{2} & \frac{1}{2} &$$

where $B = [ae\ E_c = (\ ^2hv_F)]^2$. It qualitatively agrees with the experimental data in Ref. [4,5]. Because the factor a depends upon the structure of the quantum point contact, and the electrostatic energy E_c is determined by the structure of the quantum dot, the fractional Coulomb blockade peak splitting is not universal in the weak backward scattering 0 < j = 2, it is universal.

In sum mary, by using the bosonization method and the unitary transformation, we have shown that the tunneling conductance between two quantum dots has the linear temperature dependence in the low energy and low temperature limit, and given a general relation between the dimensionless tunneling conductance g and the fractional Coulomb blockade peak splitting f which is valid both for the weak and strong backward scattering of the electrons on the impurity. Our treatment of this kind of system is simple and elective, and can be used to study other similar problems because it can exactly treat the backward scattering potential which is a relevant term in the low energy region, the usual perturbation expansion methods of this term may fail because the high orders are divergent in the low energy limit.

W e are very grateful to Prof. Peter Fulde for his encouragement.

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